

CY7C1069GN

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Selection Guide

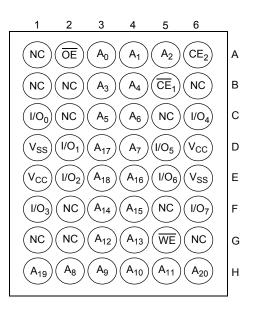
Description	-10	Unit
Maximum access time	10	ns
Maximum operating current	110	mA
Maximum CMOS standby current	30	mA

Pin Configurations

Figure 1. 54-pin TSOP II pinout (Top View)^[1]

				1	
NC		1	54	þ	NC
V_{CC}		2	53		V_{SS}
NC		3	52	þ	NC
I/O ₆		4	51		I/O ₅
V_{SS}		5	50		V_{CC}
I/O7		6	49		I/O ₄
A_4		7	48	Ь	A ₅
A ₃		8	47	Б	A ₆
A ₂	Г	9	46	h	A ₇
A ₁		10	45	Б	А ₈
A ₀		11	44	Б	A ₉
NČ		12	43	Ь	NC
CE₁		13	42		OE
V _{CC}		14	41	Б	V_{SS}
WE		15	40		NC
CE_2		16	39		A ₂₀
A ₁₉		17	38		A ₁₀
A ₁₈		18	37		A ₁₁
A ₁₇		19	36		A ₁₂
A ₁₆		20	35		A ₁₃
A ₁₅		21	34	Þ	A ₁₄
I/O ₀		22	33		I/O ₃
V _{CC}		23	32	\square	V_{SS}
I/O ₁		24	31	\square	I/O ₂
NC		25	30		NC
V_{SS}		26	29	Р	V_{CC}
NC		27	28	Ρ	NC

Figure 2. 48-ball VFBGA pinout (Top View) ^[1]



Note 1. NC pins are not connected on the die.



Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. These user guidelines are not tested.

Storage temperature65 °C to +150 °C
Ambient temperature with power applied–55 °C to +125 °C
Supply voltage on V_{CC} relative to GND $^{[2]}$ –0.5 V to V_{CC} + 0.5 V
DC voltage applied to outputs in High Z state $^{[2]}$ 0.5 V to V_{CC} + 0.5 V

DC input voltage [2]	–0.5 V to V_{CC} + 0.5 V
Current into outputs (LOW)	
Static discharge voltage (MIL-STD-883, method 3015)	>2001 V
Latch-up current	> 140 mA

Operating Range

Range	Ambient Temperature	V _{cc}
Industrial	–40 °C to +85 °C	$3.3~V\pm0.3~V$

DC Electrical Characteristics

Over the Operating Range

Parameter	Deeg	Description	Toot Conditions	-10ns			Unit
Parameter	Desc	npuon	Test Conditions	Min	Typ ^[3]	Max	Unit
V _{OH}	Output HIGH	2.2 V to 2.7 V	Min V _{CC} , I _{OH} = -1.0 mA	2.0	-	-	V
	voltage	2.7 V to 3.0 V	Min V _{CC} , I _{OH} = -4.0 mA	2.2	-	-	
		3.0 V to 3.6 V	Min V _{CC} , I _{OH} = -4.0 mA	2.4	-	-	
V _{OL}	Output LOW	2.2 V to 2.7 V	Min V _{CC} , I_{OL} = 2.0 mA	-	-	0.4	V
	voltage	2.7 V to 3.6 V	Min V _{CC} , I _{OL} = 8.0 mA	-	_	0.4	
V _{IH}	Input HIGH	2.2 V to 2.7 V	-	2.0	_	V _{CC} + 0.3	V
	voltage	2.7 V to 3.6 V	-	2.0	_	V _{CC} + 0.3	
V _{IL}	Input LOW	2.2 V to 2.7 V	-	-0.3	_	0.6	V
	voltage ^[2]	2.7 V to 3.6 V	-	-0.3	_	0.8	
I _{IX}	Input leakage c	urrent	$GND \leq V_{IN} \leq V_{CC}$	–1		+1	μA
I _{OZ}	Output leakage	current	GND \leq V _{OUT} \leq V _{CC} , Output disabled	-1		+1	μA
I _{CC}	V _{CC} operating s	supply current	V _{CC} = Max, f = f _{MAX} = 1/t _{RC} , I _{OUT} = 0 mA, CMOS levels	-	90	110	mA
I _{SB1}	Automatic CE p current – TTL ir		$\begin{array}{l} \text{Max } V_{CC}, \ \overline{CE}_1 \geq V_{IH}, \ CE_2 \leq V_{IL}, \\ V_{IN} \geq V_{IH} \ \text{or} \ V_{IN} \leq V_{IL}, \ f = f_{MAX} \end{array}$	-	-	40	mA
I _{SB2}	Automatic CE p current – CMOS		$\begin{array}{l} \underline{Max} \ V_{CC}, \\ CE_1 \geq V_{CC} - 0.3 \ V, \ CE_2 \leq 0.3 \ V, \\ V_{IN} \geq V_{CC} - 0.3 \ V \ or \ V_{IN} \leq 0.3 \ V, \ f = 0 \end{array}$	_	20	30	mA

Notes

V_{IL(min)} = -2.0 V and V_{IH(max)} = V_{CC} + 2 V for pulse durations of less than 20 ns.
 Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = 3 V (for V_{CC} range of 2.2 V–3.6 V)



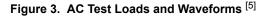
Capacitance

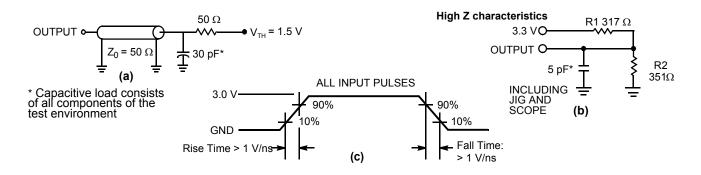
Parameter ^[4]	Description	Test Conditions	TSOP II	VFBGA	Unit
C _{IN}	Input capacitance	T _A = 25 °C, f = 1 MHz, V _{CC} = 3.3 V	10	10	pF
C _{OUT}	IO capacitance		10	10	pF

Thermal Resistance

Parameter ^[4]	Description	Test Conditions	TSOP II	VFBGA	Unit
- JA		Still air, soldered on a 3 × 4.5 inch, four layer printed circuit board	93.63	31.50	°C/W
- 30	Thermal resistance (junction to case)		21.58	15.75	°C/W

AC Test Loads and Waveforms





Notes

4. Tested initially and after any design or process changes that may affect these parameters.

5. Full device AC operation assumes a 100-µs ramp time from 0 to V_{CC(min)} and 100-µs wait time after V_{CC} stabilization.



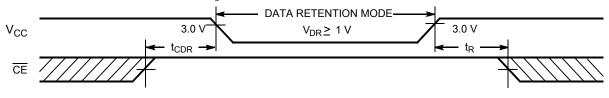
Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions	Min	Max	Unit
V _{DR}	V_{CC} for data retention	_	1.0	-	V
I _{CCDR}	Data retention current	$\begin{array}{l} V_{CC} = V_{DR}, \overline{CE}_1 \geq V_{CC} - 0.2 \text{ V}, CE_2 \leq 0.2 \text{ V}, \\ V_{IN} \geq V_{CC} - 0.2 \text{ V} \text{ or } V_{IN} \leq 0.2 \text{ V} \end{array}$	_	30	mA
t _{CDR} ^[6]	Chip deselect to data retention time	_	0	_	ns
t _R ^[7]	Operation recovery time	_	10	-	ns

Data Retention Waveform

Figure 4. Data Retention Waveform



Notes
6. Tested initially and after any design or process changes that may affect these parameters.
7. Full device operation requires linear V_{CC} ramp from V_{DR} to V_{CC(min.)} > 100 μs or stable at V_{CC(min.)} > 100 μs.

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AC Switching Characteristics

Over the Operating Range

Parameter [8]	Description	-	10	Unit
Parameter	Description		Мах	Unit
Read Cycle				-
t _{power}	V _{CC} (typical) to the first access ^[9, 10]	100	-	μS
t _{RC}	Read cycle time	10	-	ns
t _{AA}	Address to data valid	-	10	ns
t _{OHA}	Data hold from address change	3	-	ns
t _{ACE}	CE ₁ LOW/CE ₂ HIGH to data valid	-	10	ns
t _{DOE}	OE LOW to data valid	-	5	ns
t _{LZOE}	OE LOW to low Z [11, 12, 13]	0	-	ns
t _{HZOE}	OE HIGH to high Z ^[11, 12, 13]	-	5	ns
t _{LZCE}	CE ₁ LOW/CE ₂ HIGH to low Z ^[11, 12, 13]	3	-	ns
t _{HZCE}	CE ₁ HIGH/CE ₂ LOW to high Z ^[11, 12, 13]	-	5	ns
t _{PU}	CE ₁ LOW/CE ₂ HIGH to power-up ^[10]	0	-	ns
t _{PD}	CE ₁ HIGH/CE ₂ LOW to power-down ^[10]	-	10	ns
Write Cycle [14	, 15]			-
t _{WC}	Write cycle time	10	-	ns
t _{SCE}	CE ₁ LOW/CE ₂ HIGH to write end	7	-	ns
t _{AW}	Address setup to write end	7	-	ns
t _{HA}	Address hold from write end	0	-	ns
t _{SA}	Address setup to write start	0	-	ns
t _{PWE}	WE pulse width	7	-	ns
t _{SD}	Data setup to write end	5	-	ns
t _{HD}	Data hold from write end	0	-	ns
t _{LZWE}	WE HIGH to low Z [11, 12, 13]	3	-	ns
t _{HZWE}	WE LOW to high Z [11, 12, 13]	_	5	ns

Notes

8. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, and input pulse levels of 0 to 3.0 V. Test conditions for the read cycle use output loading shown in (a) of Figure 3 on page 5, unless specified otherwise.

9. t_{POWER} gives the minimum amount of time that the power supply is at typical V_{CC} values until the first memory access is performed.

10. These parameters are guaranteed by design and are not tested.

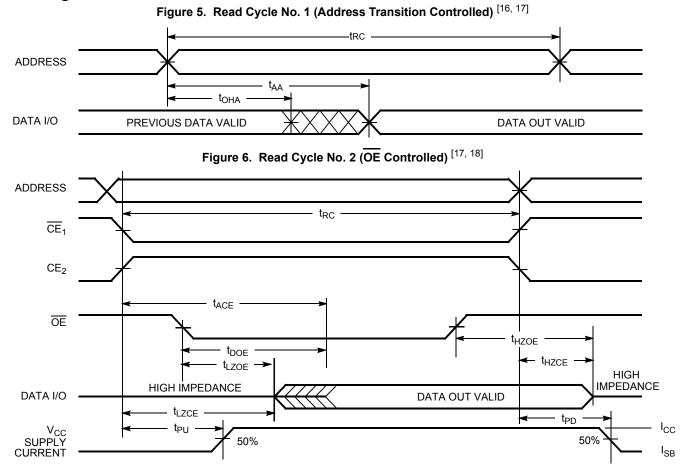
t_{HZOE}, t_{HZOE}, t_{LZOE}, t_{LZCE}, and t_{LZWE} are specified with a load capacitance of 5 pF as in (b) of Figure 3 on page 5. Transition is measured ±200 mV from steady state voltage.
 At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZDE}, t_{HZDE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any device. These parameters are guaranteed by design and are not tested.

13. Tested initially and after any design or process changes that may affect these parameters.

14. The internal write time of the memory is defined by the overlap of WE, CE₁ = V_{IL}, and CE₂ = V_{IH}. CE₁ and WE are LOW along with CE₂ HIGH to initiate a write, and the transition of any of these signals can terminate. The input data setup and hold timing should be referenced to the edge of the signal that terminates the write.
 15. The minimum write cycle time for Write Cycle No. 2 (WE Controlled, OE LOW) is the sum of t_{HZWE} and t_{SD}.



Switching Waveforms

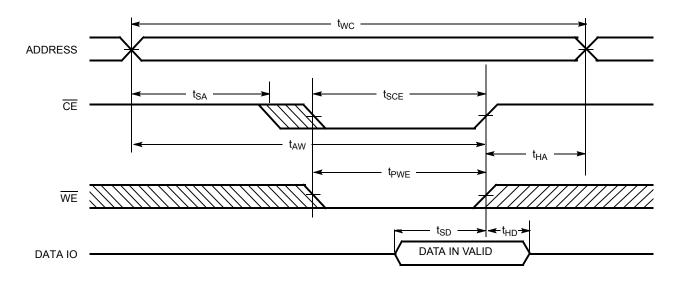


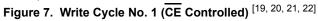
Notes

- 16. The device is continuously selected. $\overline{CE}_1 = V_{IL}$, and $CE_2 = V_{IH}$. 17. WE is HIGH for read cycle.
- 18. Address valid before or similar to \overline{CE}_1 transition LOW and CE_2 transition HIGH.

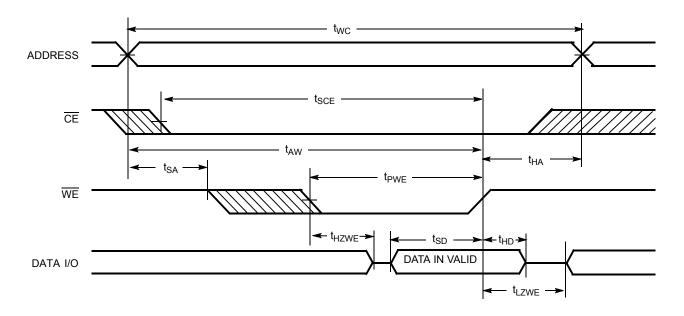


Switching Waveforms (continued)









Notes

- 19. CE is a shorthand combination of both CE₁ and CE₂ combined. It is active LOW.
 20. Data I/O is high impedance if OE = V_{IH}.
 21. If CE goes HIGH simultaneously with WE going HIGH, the output remains in a high impedance state.
 22. The internal write time of the memory is defined by the overlap of WE = VIL, CE = VIL. These signals must be LOW to initiate a write, and the HIGH transition of any of these signals can terminate the operation. The input data setup and hold timing should be referenced to the edge of the signal that terminates the write.



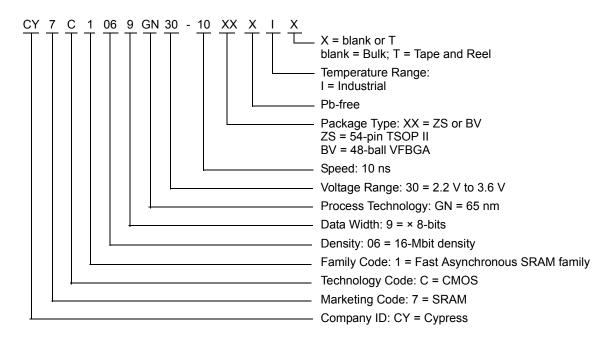
Truth Table

CE ₁	CE ₂	OE	WE	I/O ₀ –I/O ₇	Mode	Power
Н	Х	Х	Х	High Z	Power-down	Standby (I _{SB})
Х	L	Х	Х	High Z	Power-down	Standby (I _{SB})
L	Н	L	Н	Data out	Read all bits	Active (I _{CC})
L	Н	Х	L	Data in	Write all bits	Active (I _{CC})
L	Н	Н	Н	High Z	Selected, outputs disabled	Active (I _{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
10	CY7C1069GN30-10ZSXI	51-85160	54-pin TSOP II (Pb-free)	Industrial
	CY7C1069GN30-10ZSXIT	51-85160	54-pin TSOP II (Pb-free), Tape and Reel	
	CY7C1069GN30-10BVXI	51-85150	48-ball VFBGA (Pb-free)	
	CY7C1069GN30-10BVXIT	51-85150	48-ball VFBGA (Pb-free), Tape and Reel	

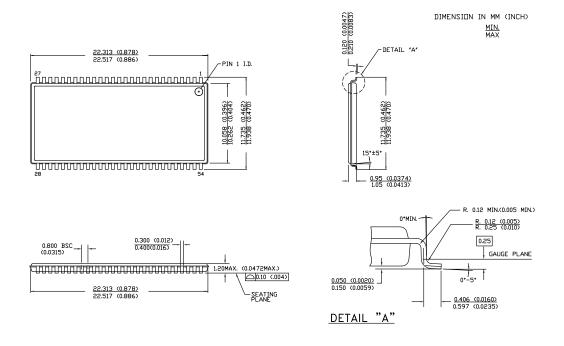
Ordering Code Definitions





Package Diagrams

Figure 9. 54-pin TSOP II (22.4 × 11.84 × 1.0 mm) Z54-II Package Outline, 51-85160



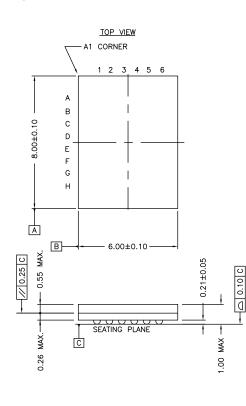
51-85160 *E

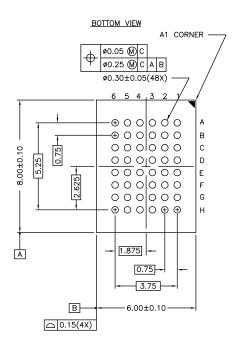




Package Diagrams (continued)

Figure 10. 48-ball VFBGA (6 × 8 × 1.0 mm) BV48/BZ48 Package Outline, 51-85150





NOTE:

PACKAGE WEIGHT: See Cypress Package Material Declaration Datasheet (PMDD) posted on the Cypress web.

51-85150 *H



Acronyms

Acronym	Description
CE	chip enable
CMOS	complementary metal oxide semiconductor
I/O	input/output
OE	output enable
SRAM	static random access memory
VFBGA	very fine-pitch ball grid array
TSOP	thin small outline package
TTL	transistor-transistor logic
WE	write enable

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
μA	microampere
μ s	microsecond
mA	milliampere
ns	nanosecond
Ω	ohm
%	percent
pF	picofarad
V	volt
W	watt



Document History Page

Document Title: CY7C1069GN, 16-Mbit (2M × 8) Static RAM

Document Number: 002-00046				
Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change
**	4948206	NILE	10/13/2015	New data sheet
*A	5437942	NILE	09/15/2016	Updated DC Electrical Characteristics: Removed Operating Range "2.7 V to 3.6 V" and all values corresponding to V_{OH} parameter. Included Operating Ranges "2.7 V to 3.0 V" and "3.0 V to 3.6 V" and all values corresponding to V_{OH} parameter. Updated Ordering Information: Updated part numbers. Updated Ordering Code Definitions. Updated to new template. Completing Sunset Review.
*B	5999403	AESATMP8	12/19/2017	Updated logo and Copyright.



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